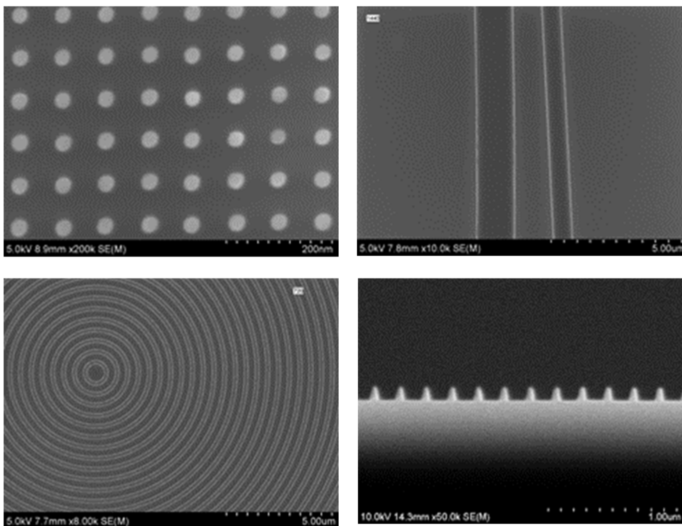
DisChem
CHEMISTRY FOR ADVANCED LITHOGRAPHY

RESIST MATERIALS

H-SiQ

Negative Tone EBL Resist

Hydrogen Silesquioxane (HSQ)

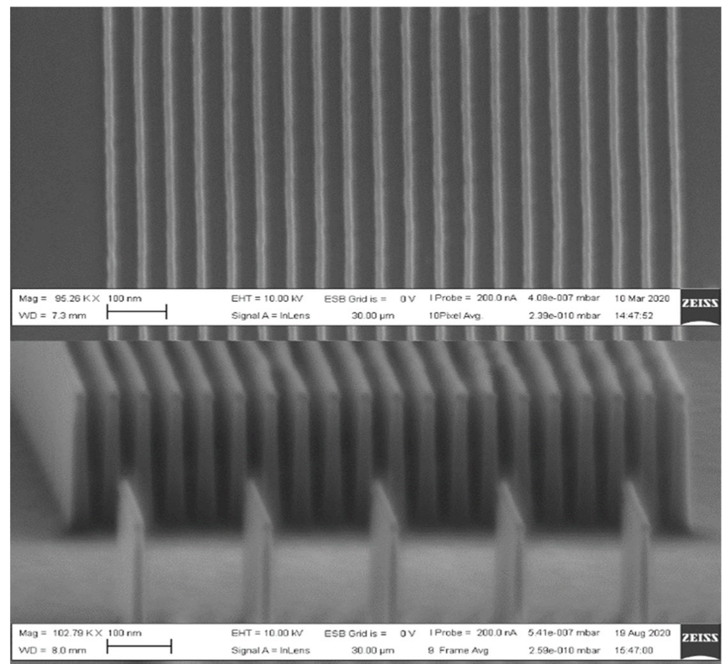


- Excellent pitch resolution, sensitivity and etch resistance for direct write thin film EBL applications.
- Prepared in MIBK in concentrations ranging from 1 – 20% wt/vol for film thicknesses 25—850 nm
- Ready to use. Immediate availability with 100% shelf life.

nEBL3 Negative Tone Resist

Hard Mask in a Bottle

SCI-TRON nEBL3 is an advanced negative tone organo-metallic resist with extremely high etch resistance and low line edge roughness that allows for EBL direct write of a chromium hard mask in a single step. nEBL3 is ideal for next generation EUV photomasks. Exclusive distribution in North America by DisChem, Inc.



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